



2SA1201

PNP SILICON TRANSISTOR

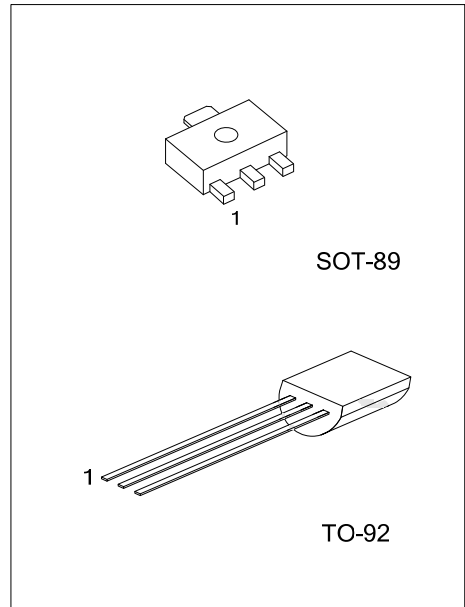
SILICON PNP EPITAXIAL TRANSISTOR

■ DESCRIPTION

The UTC **2SA1201** is designed for power amplifier and voltage amplifier applications.

■ FEATURES

- *High voltage: $V_{CEO} = -120V$
- *High transition frequency: $f_T = 120MHz$ (typ.)
- * $P_C = 1$ to 2 W(mounted on ceramic substrate)



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
-	2SA1201G-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SA1201L-x-T92-B	2SA1201G-x-T92-B	TO-92	E	C	B	Tape Box
2SA1201L-x-T92-K	2SA1201G-x-T92-K	TO-92	E	C	B	Bulk

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>2SA1201G-x-AB3-R</p>	<p>(1) R: Tape Reel, B: Tape Box, K: Bulk (2) AB3: SOT-89, T92: TO-92 (3) x: refer to Classification of h_{FE} (4) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING

SOT-89	TO-92

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	-120	V
Collector-Emitter Voltage		V_{CEO}	-120	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		I_C	-800	mA
Base Current		I_B	-160	mA
Collector Power Dissipation	SOT-89	P_C	500	mW
			1000 (Note 2)	mW
	TO-92		600	mW
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Mounted on cermic substrate($250\text{mm}^2 \times 0.8\text{t}$)

■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}$, $I_B = 0$	-120			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}$, $I_C = 0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -120\text{V}$, $I_E = 0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -5\text{V}$, $I_C = -100\text{mA}$	80		240	
Collector to Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$			-1.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE} = -5\text{V}$, $I_C = -100\text{mA}$			-1.0	V
Transition Frequency	f_T	$V_{CE} = -5\text{V}$, $I_C = -100\text{mA}$		120		MHz
Collector Output Capacitance	C_{OB}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$			30	pF

■ CLASSIFICATION OF h_{FE}

RANK	O	Y
RANGE	80 - 160	120 - 240

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